

IN THE CLAIMS

Claims 1-30 (Canceled)

31. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

providing a film substrate having a main surface, a rear surface opposing to the main surface, a plurality of device forming areas of the main surface and electrode members individually separated from one another and formed on the device forming areas;

providing a plurality of semiconductor chips each having a main surface and electrodes formed on the main surface thereof;

arranging the semiconductor chips on respective ones of the device forming areas and electrically connecting the electrodes of the semiconductor chips with electrode members on the respective device forming areas;

forming a resin encapsulator collectively sealing the plurality of device forming areas, the electrode members and the semiconductor chips; and

~~cutting the resin encapsulator and the film substrate between adjacent device forming areas by dicing,~~

separating the resin encapsulator from the film substrate
and thereby revealing the electrode members on one side of the
resin encapsulator;

wherein the electrode members are spaced from a cutting
side surface resulting from the cutting step of the resin
encapsulator.

Claim 32 (Canceled)

33. (Currently Amended) A method of manufacturing a semiconductor device according to claim 32 31, wherein the cutting step includes a step of sticking dicing tape on another side of the resin encapsulator, wherein the another side is opposed to the one side of the resin encapsulator.

34. (Currently Amended) A method of manufacturing a semiconductor device according to claim 32 31, further comprising a step of plating the revealed electrode members, after the step of separating the resin encapsulator.

35. (Previously Presented) A method of manufacturing a semiconductor device according to claim 34, wherein the plating step is performed before the cutting step.